



# DGW20N65CTL0

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**RoHS**  
COMPLIANT

**Electrical Characteristics of the IGBT**  $T_j=25$  unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Collector-Emitter Breakdown Voltage	$BV_{CES}$	$V_{GE}=0V, I_C$	650		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1mA$	5.0	5.8	6.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=20A$ $T_j=25^\circ C,$ $T_j=125^\circ C$ $T_j=150^\circ C$		1.60 1.75 1.80	1.95	V
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{CE}=600V, V_{GE}=0V$ $T_j=25^\circ C,$ $T_j=150^\circ C$			0.25 1.00	mA
Gate-Emitter Leakage Current	$I_{GES}$	$V_{CE}=0V, V_{GE}=\pm 20V$			$\pm 200$	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic</b>						

Input Capacitance

 $C_{ies}$ 

V



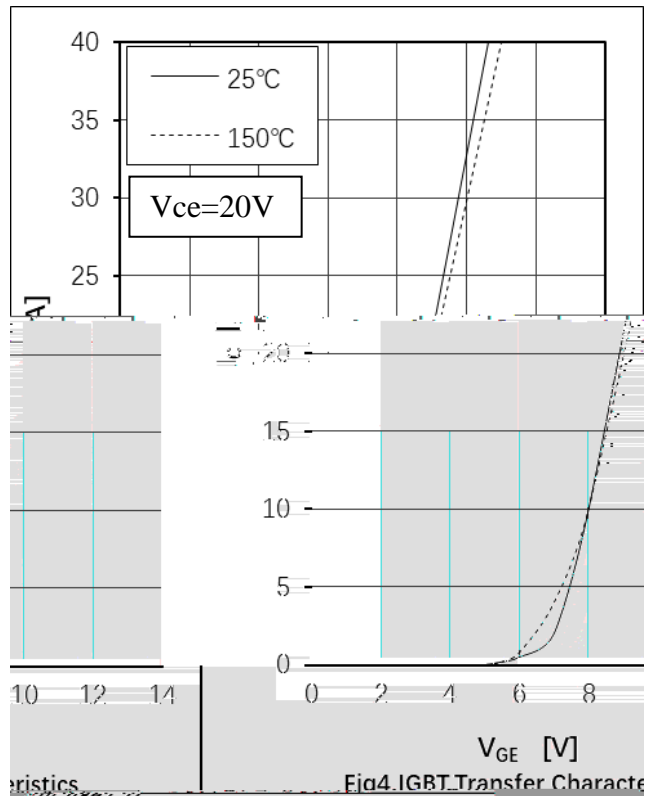
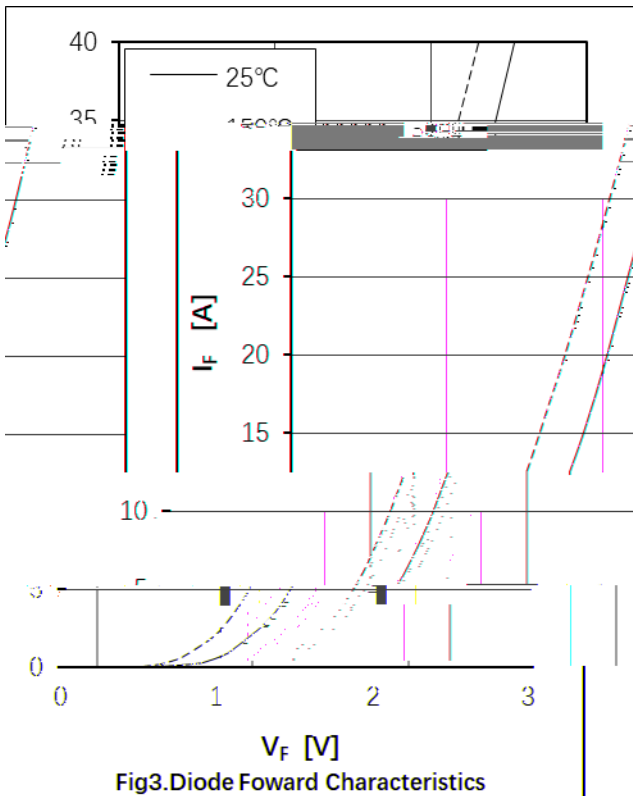
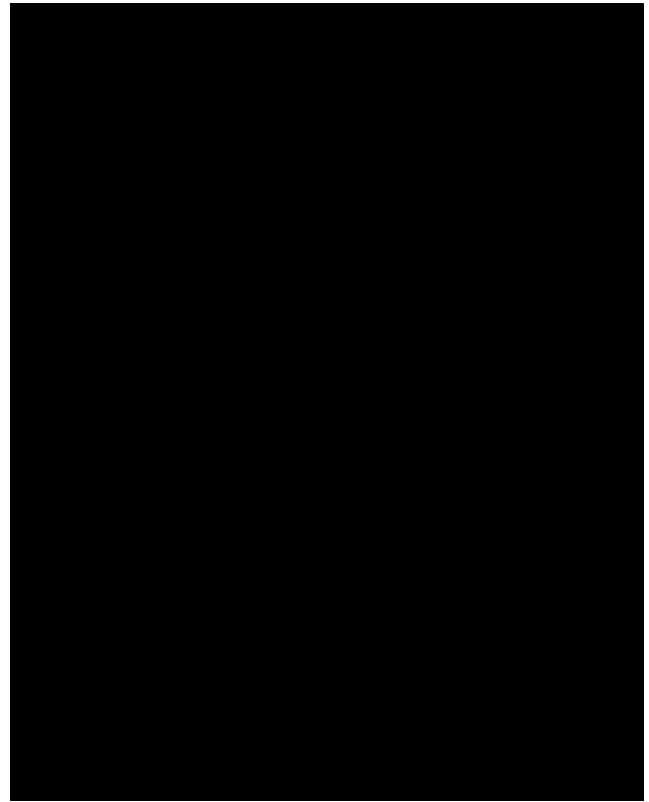
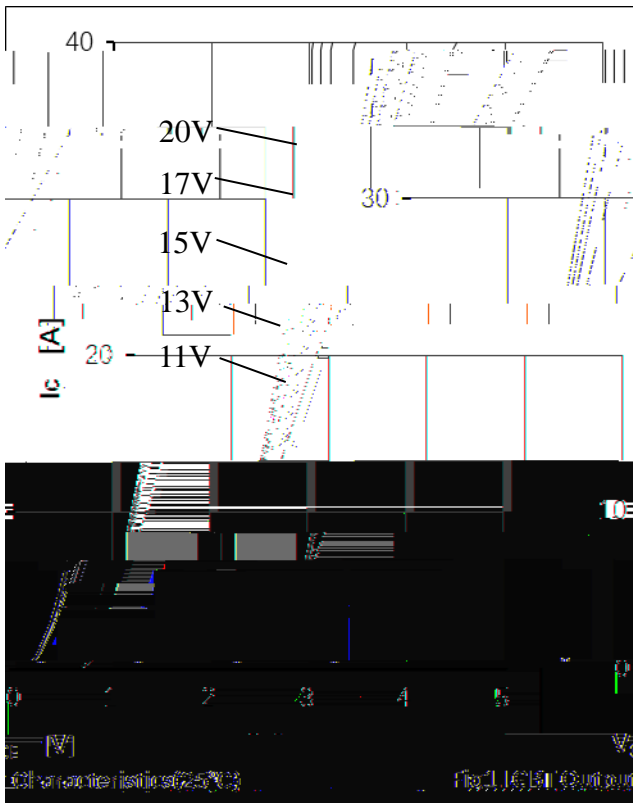


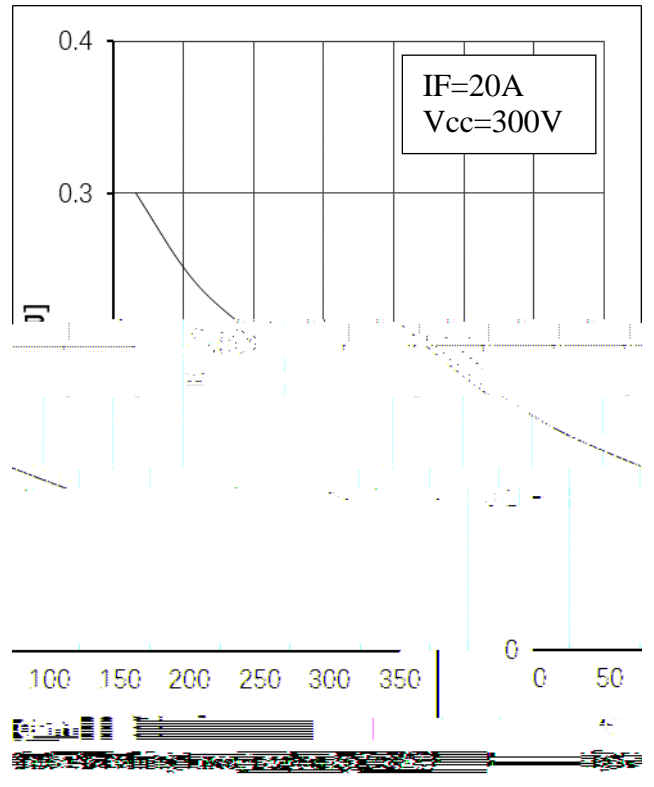
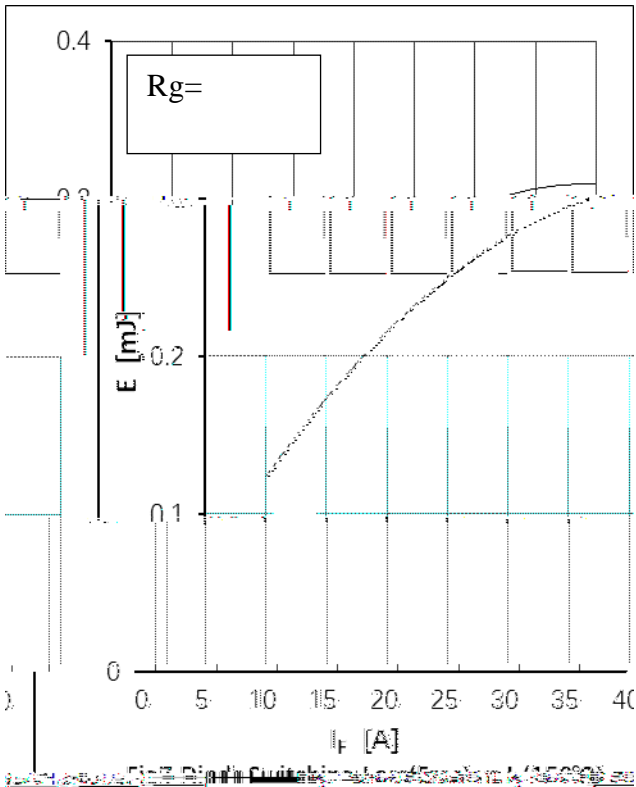
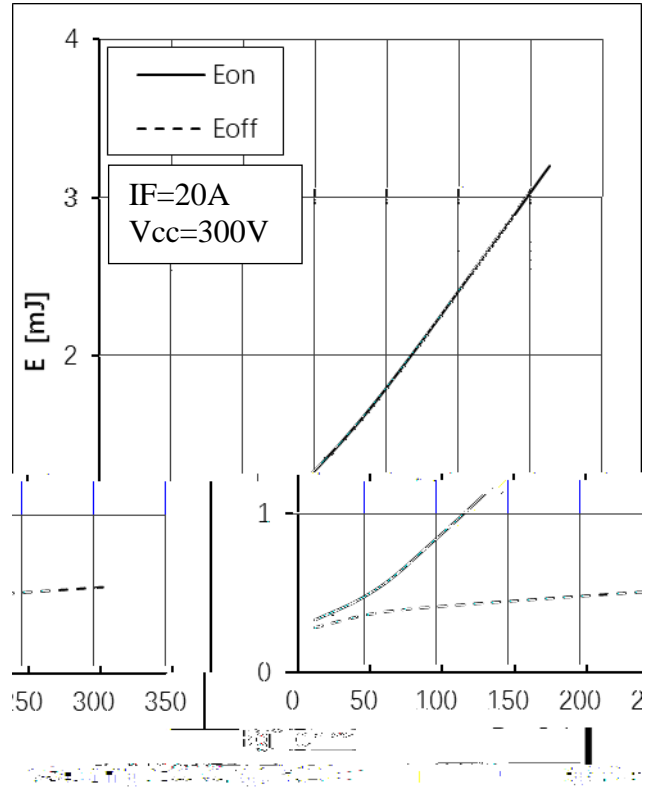
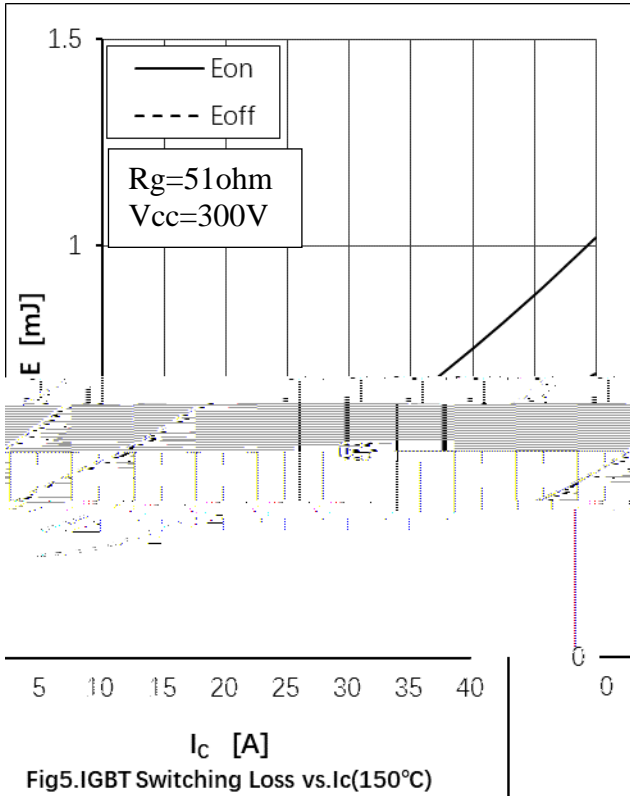
# DGW20N65CTL0

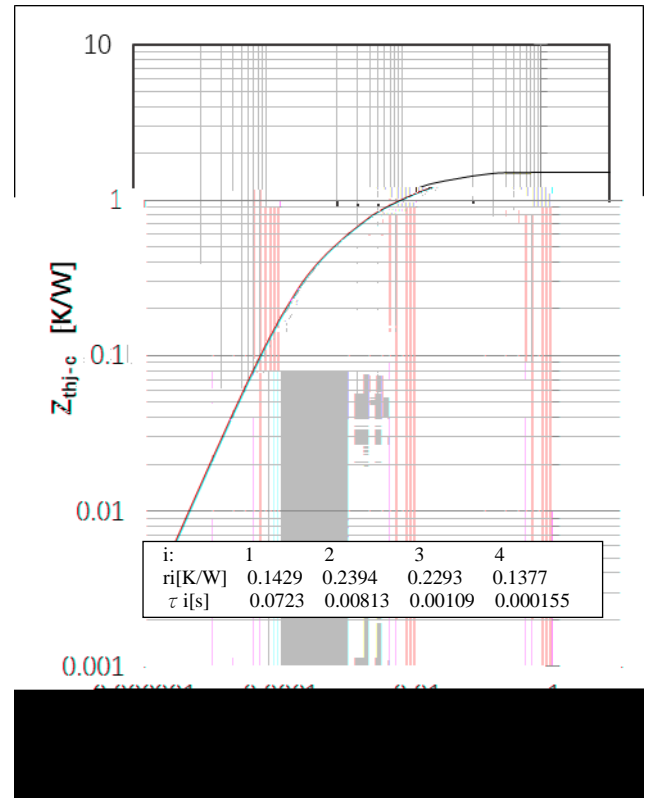
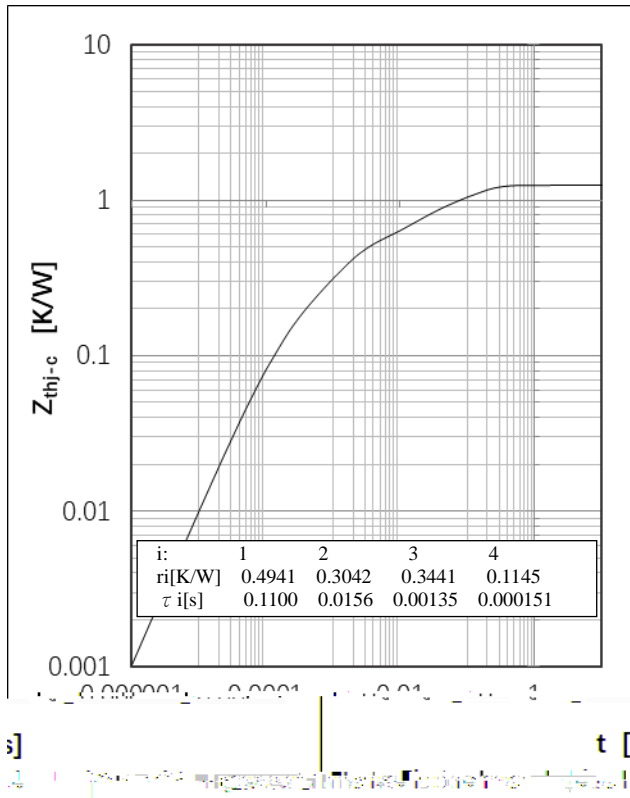
**RoHS**  
COMPLIANT

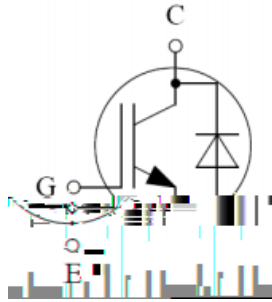
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Electrical









## Package Outline Information

TO-247AB	
Dim	Min